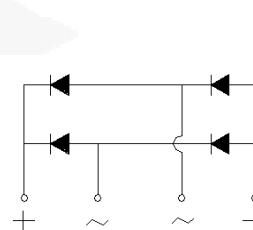


Single Phase Silicon Bridge Rectifier

V_{RRM} = 600 V - 1000 V
I_O = 10 A

Features

- Low forward voltage drop
- Low leakage current
- Types from 600 V up to 1000 V V_{RRM}
- Not ESD Sensitive



BR-10 Package



Mechanical Data

Case: Molded plastic body

Polarity: marked on the body

Mounting: Hole thru for #6 screw

Mounting position: Any

Maximum ratings at T_c = 25 °C, unless otherwise specified

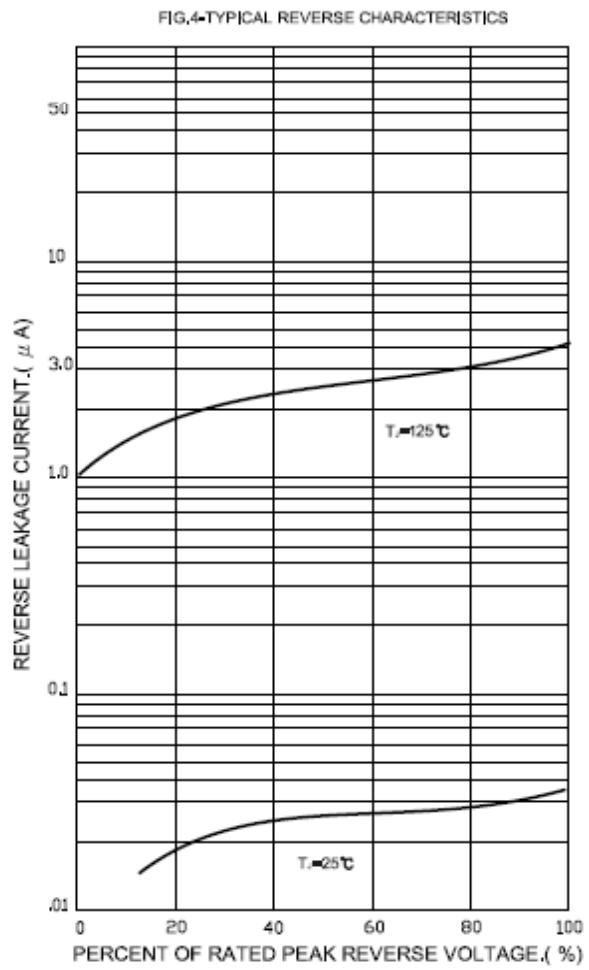
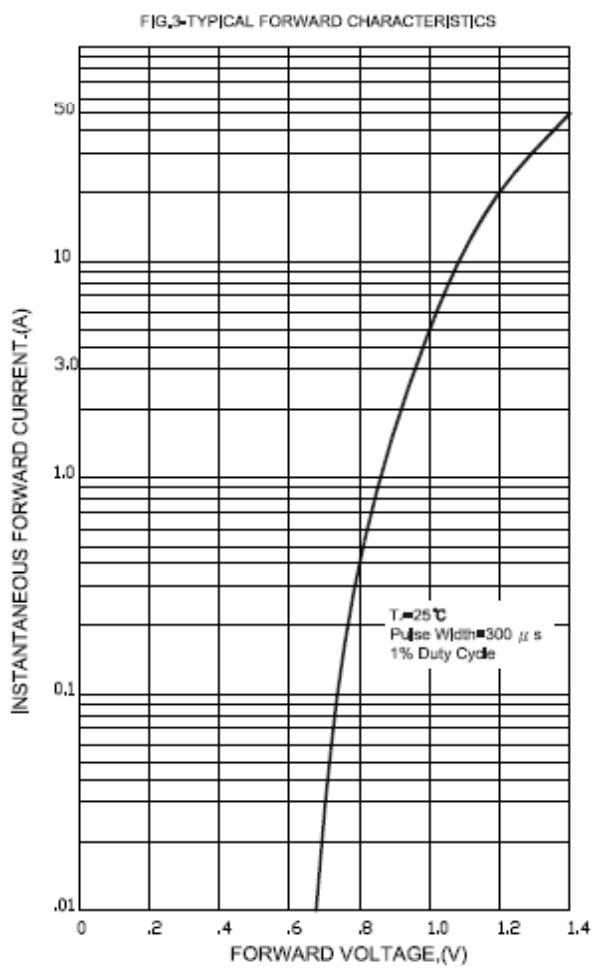
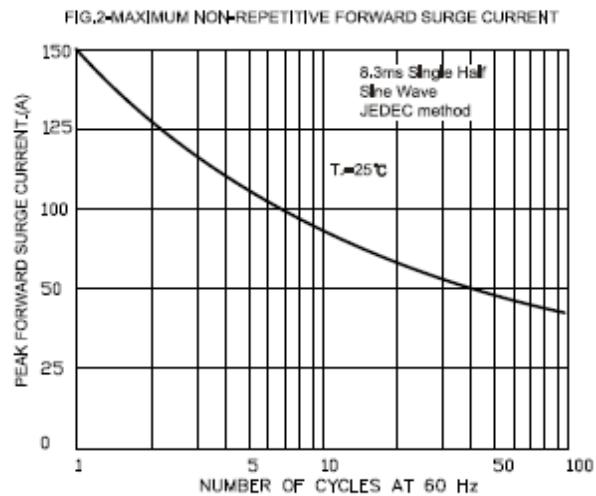
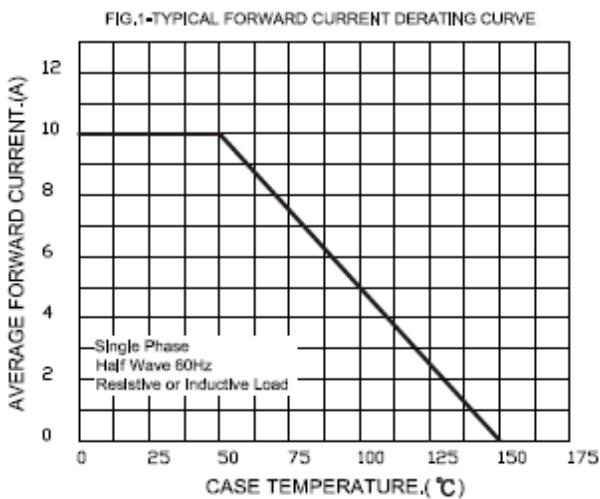
Parameter	Symbol	Conditions	BR106	BR108	BR1010	Unit
Repetitive peak reverse voltage	V _{RRM}		600	800	1000	V
RMS reverse voltage	V _{RMS}		420	560	700	V
DC blocking voltage	V _{DC}		600	800	1000	V
Operating temperature	T _j		-55 to 150	-55 to 150	-55 to 150	°C
Storage temperature	T _{stg}		-55 to 150	-55 to 150	-55 to 150	°C

Electrical characteristics at T_c = 25 °C, unless otherwise specified

Single phase, half sine wave, 60 Hz, resistive or inductive load

For capacitive load derate current by 20%

Parameter	Symbol	Conditions	BR106	BR108	BR1010	Unit
Maximum average forward rectified current	I _O	T _c = 50 °C	10	10	10	A
Peak forward surge current	I _{FSM}	t _p = 8.3 ms, half sine	150	150	150	A
Maximum instantaneous forward voltage drop per bridge element	V _F	I _F = 5.0 A	1.1	1.1	1.1	V
Maximum DC reverse current at rated DC blocking voltage	I _R	T _a = 25 °C T _a = 100 °C	10 1000	10 1000	10 1000	µA
Typical junction capacitance	C _j		55	55	55	pF
Typical thermal resistance	R _{θJA}		9.4	9.4	9.4	°C/W



Package dimensions and terminal configuration

Product is marked with part number and terminal configuration.

